

Descriptions

This 100V,59A N-Channel MOSFET in a TO-252 Plastic Package.

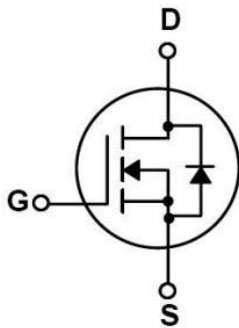
Features

- Low On-Resistance
- Fast switching
- Halogen-free Product

Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

Equivalent Circuit



Pinning



PIN1: Gate PIN 2: Drain PIN 3: Source PIN 4: Drain

Absolute Maximum Ratings(Ta=25°C)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	59	A
Pulsed Drain Current		I_{DM}	240	A
Gate-Source Voltage		V_{GSS}	± 20	V
Avalanche Current		I_{AR}	15	A
Single Pulsed Avalanche Energy		E_{AS}	170	mJ
Total Power Dissipation		$P_D(T_c=25^\circ\text{C})$	73	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Junction-to-Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	20	$^\circ\text{C/W}$
Junction-to-Ambient	Steady-State		50	
Junction-to-Case	Steady-State	$R_{\theta JC}$	1.7	

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}$ $I_D=250\mu\text{A}$	100	102		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100\text{V}$ $V_{GS}=0\text{V}$			1	μA
		$V_{DS}=100\text{V}$ $V_{GS}=0\text{V}$ $T_J=125^\circ\text{C}$			5	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$ $V_{DS}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu\text{A}$	2.0	2.6	4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ $I_D=35\text{A}$		14	18	m Ω
Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$ $I_S=35\text{A}$ $T_J=25^\circ\text{C}$			1.3	V

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1MHz$		4780		pF
Output Capacitance	C_{oss}			110		
Reverse Transfer Capacitance	C_{rss}			140		
Gate resistance	R_g	$V_{GS}=0V$, $V_{DS}=0V$, $f=1MHz$		1		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$, $V_{DS}=50V$, $I_D=20A$		16		nC
Gate Source Charge	Q_{gs}			5		
Gate Drain Charge	Q_{gd}			3		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=50V$ $R_L=2.5\Omega$ $R_{GEN}=3\Omega$		7.5		ns
Turn-On Rise Time	t_r			2.5		
Turn-Off Delay Time	$t_{d(off)}$			16.5		
Turn-Off Fall Time	t_f			3		

Electrical Characteristic Curve

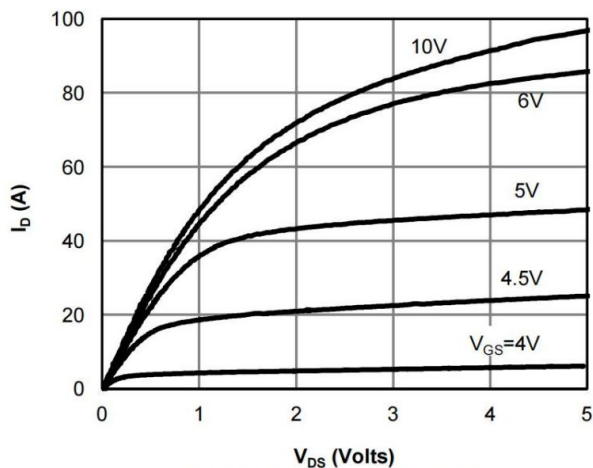


Fig 1: On-Region Characteristics

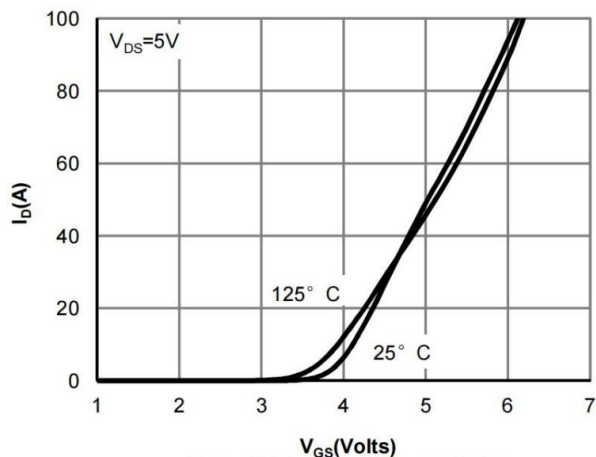


Figure 2: Transfer Characteristics

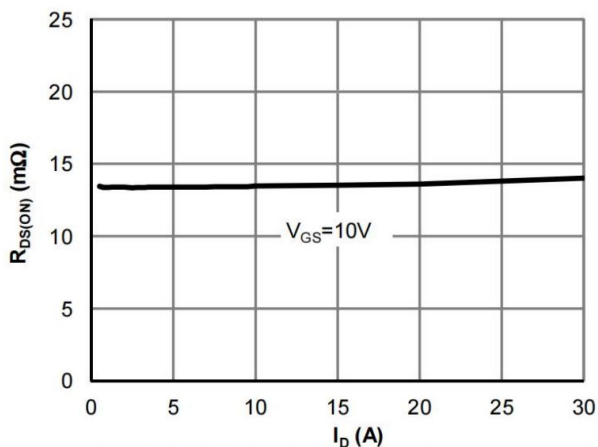


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

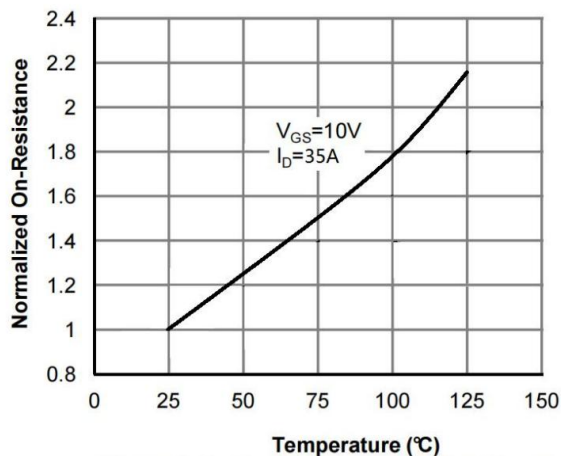


Figure 4: On-Resistance vs. Junction Temperature

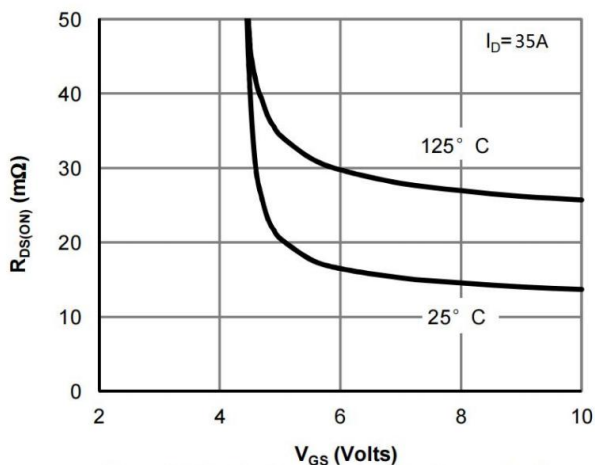


Figure 5: On-Resistance vs. Gate-Source Voltage

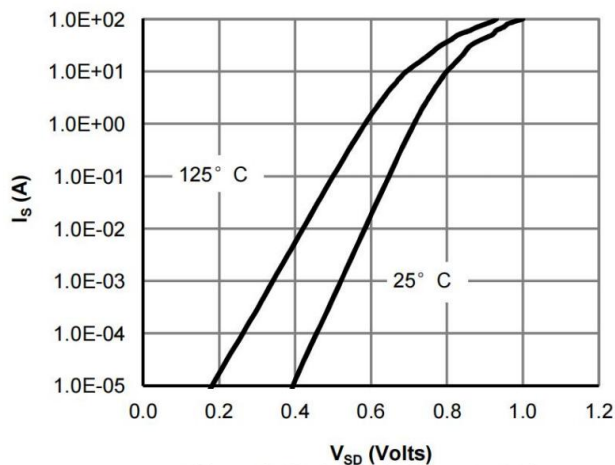


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

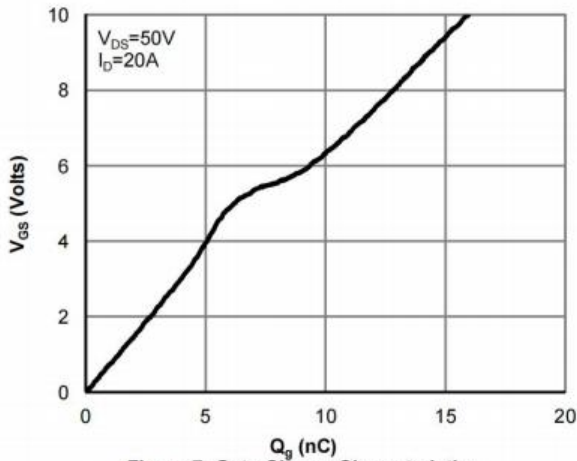


Figure 7: Gate-Charge Characteristics

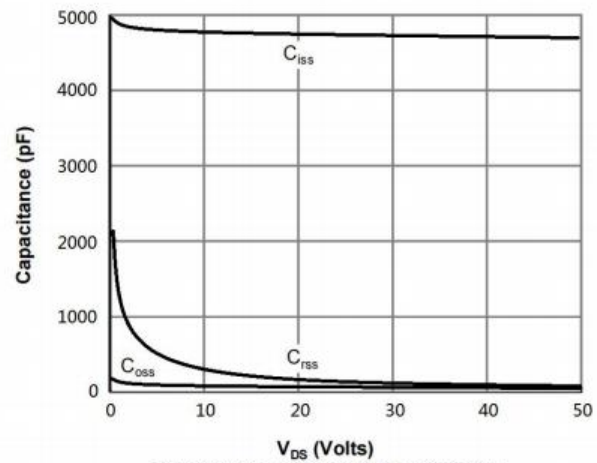


Figure 8: Capacitance Characteristics

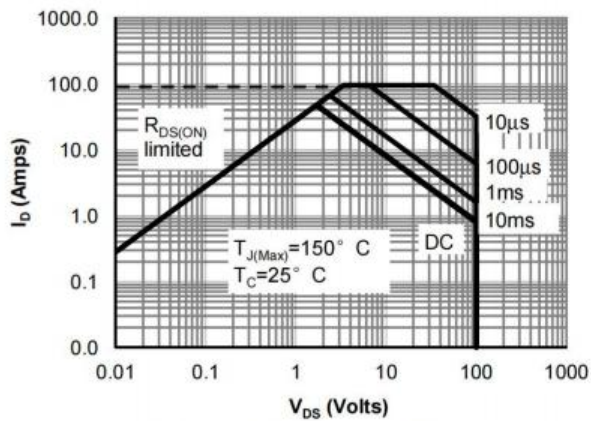


Figure 9: Maximum Forward Biased Safe Operating Area

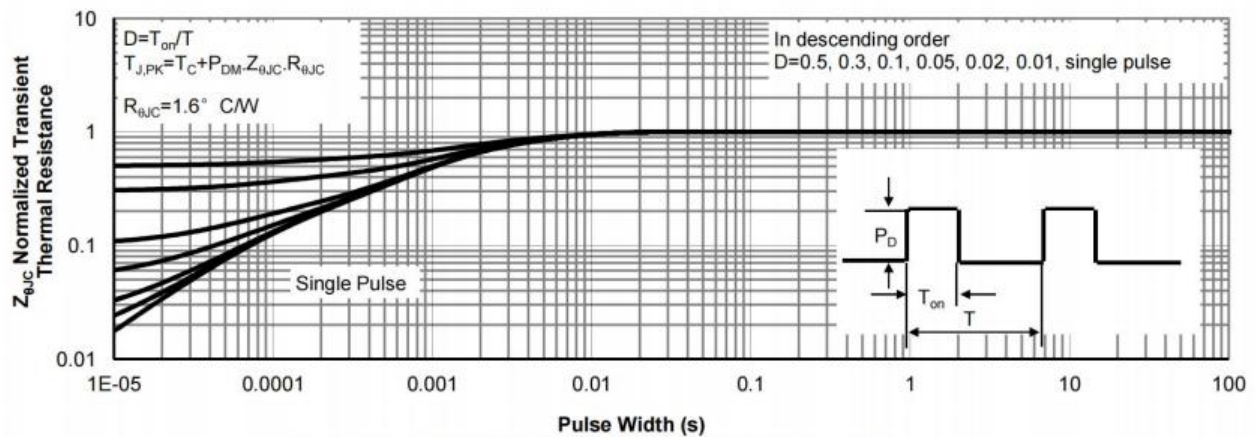
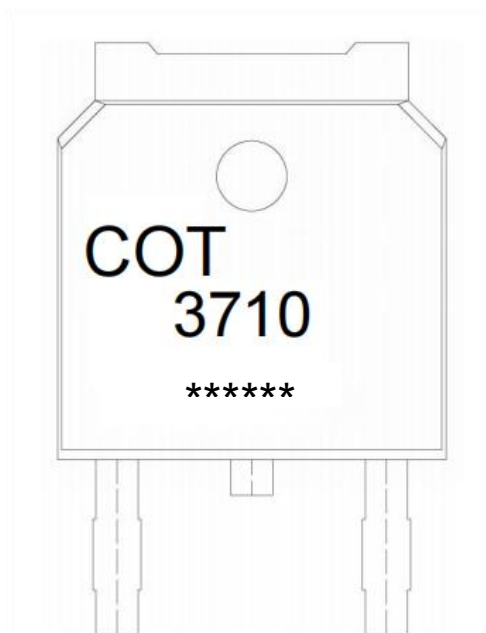


Figure 10: Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

COT: Company Code.

3710: Product Type.

*****: Lot No. Code, code change with Lot No.

Packaging SPEC

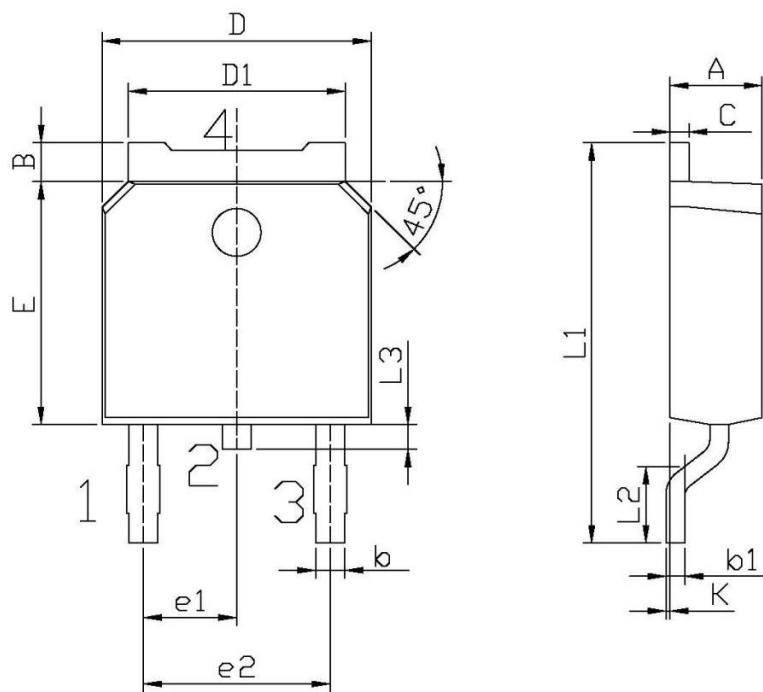
REEL INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13" × 16	360×360×50	380×335×366

TUBE INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

Package Outline Dimensions



单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252